

Silicon NPN Power Transistors

2SC4163

DESCRIPTION

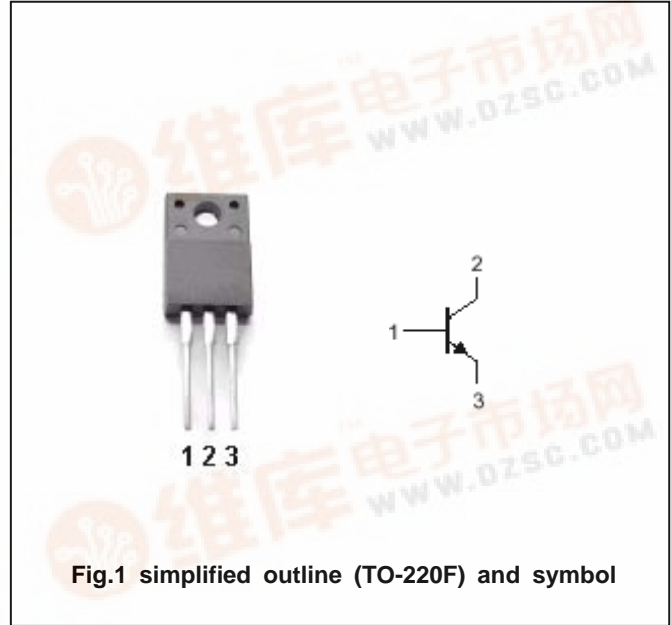
- With TO-220F package
- High breakdown voltage.
- High reliability.
- Fast switching speed
- Wide area of safe operation

APPLICATIONS

- Switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		12	A
I <sub>CM</sub>	Collector current-peak		25	A
I <sub>B</sub>	Base current		4	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	40	W
			2	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; R <sub>BE</sub> =∞	400			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	500			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A			0.8	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V ; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0			10	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1.6A ; V <sub>CE</sub> =5V	15		50	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =8A ; V <sub>CE</sub> =5V	10			
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =10mA ; V <sub>CE</sub> =5V	10			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V ; f=1MHz		160		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1.6A ; V <sub>CE</sub> =10V		20		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =10A ; I <sub>B1</sub> =2A I <sub>B2</sub> =-4A V <sub>CC</sub> =200V , R <sub>L</sub> =20 Ω			0.5	μ s
t <sub>s</sub>	Storage time				2.5	μ s
t <sub>f</sub>	Fall time				0.3	μ s

◆ h<sub>FE-1</sub> Classifications

L	M	N
15-30	20-40	30-50

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PACKAGE OUTLINE

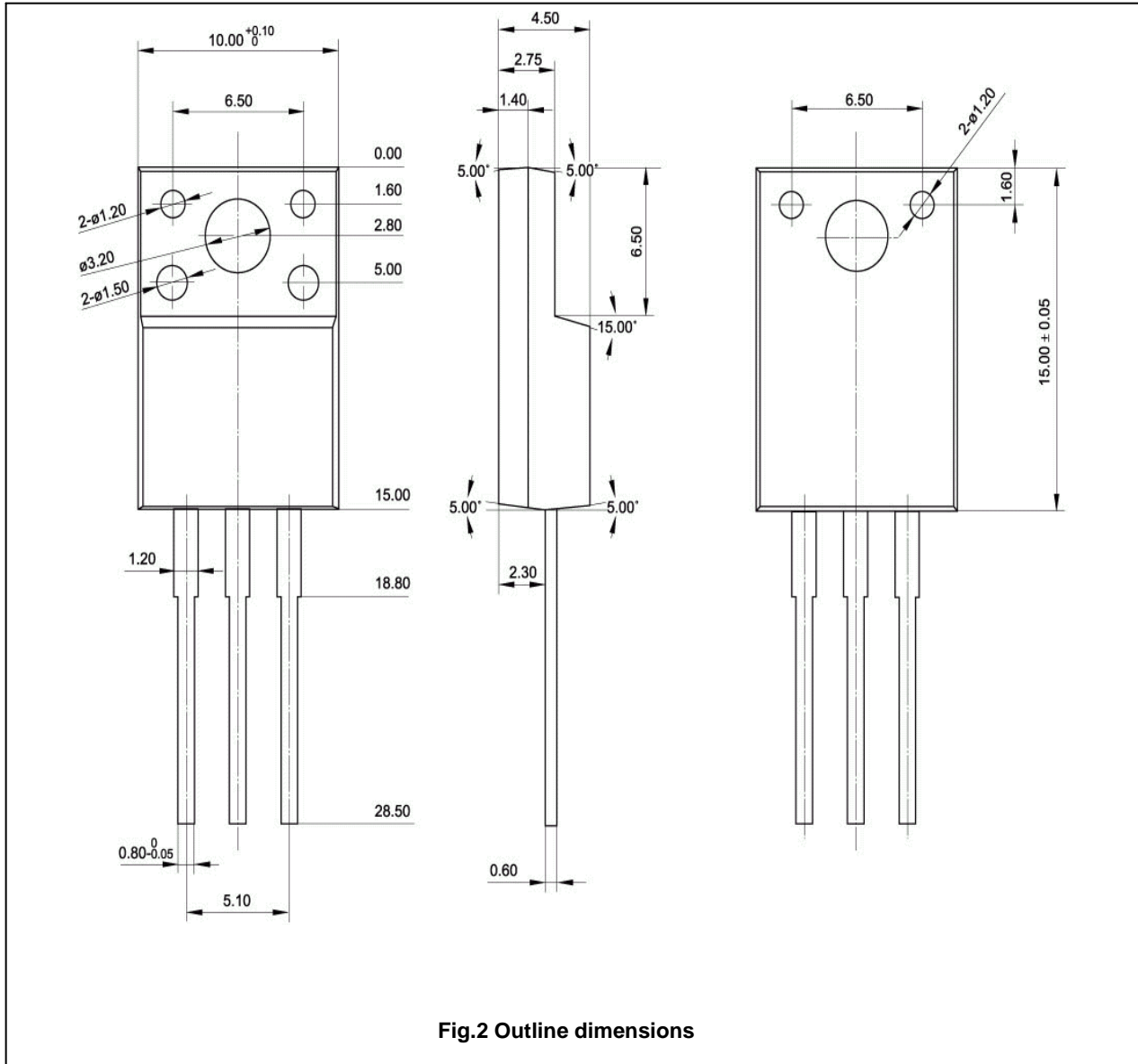


Fig.2 Outline dimensions

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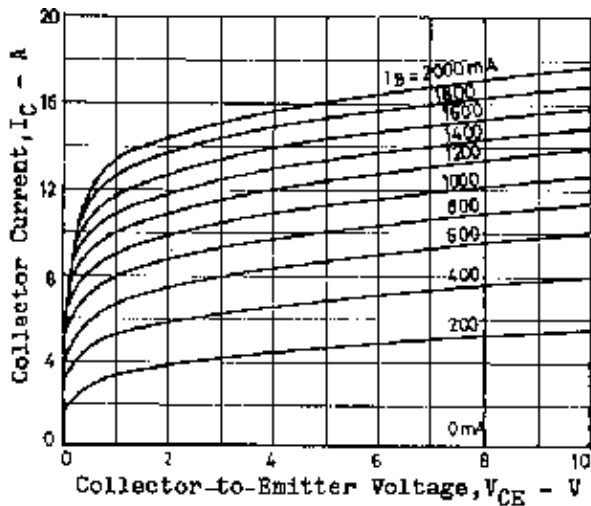


Fig.3 Static Characteristic

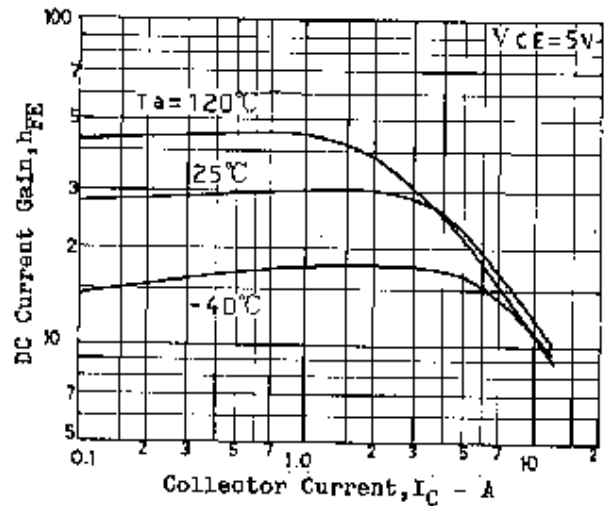


Fig.4 DC current Gain

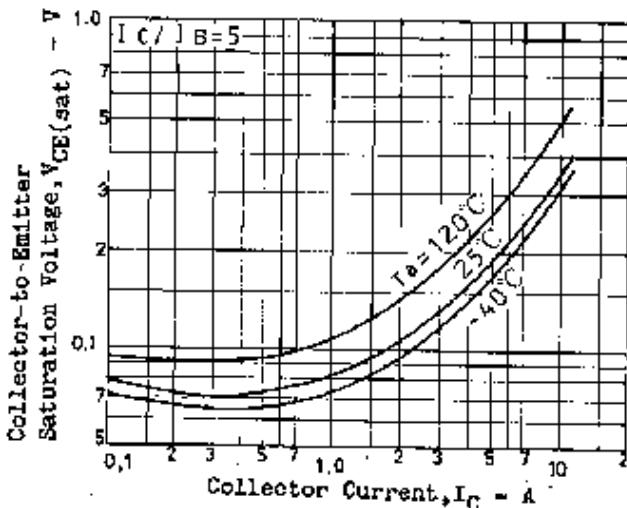


Fig.5 Collector-Emitter Saturation Voltage

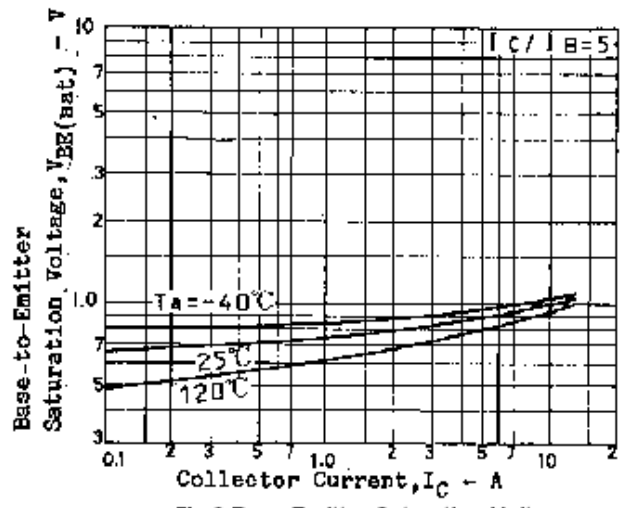


Fig.6 Base-Emitter Saturation Voltage

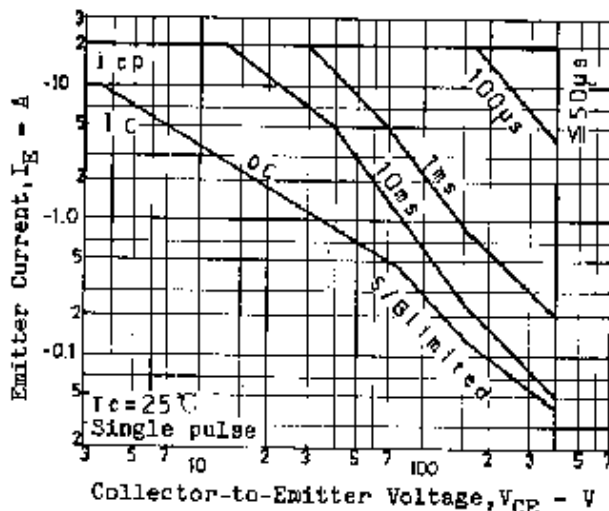


Fig.7 Safe Operating Area